













ESD

103

TSS

MOV

GDT

PLED

LMV324IDR(MS)

Product specification





GENERAL DESCRIPTION

The LMV324IDR(MS) (quad)are general purpose,I ow offset,high frequency response andlow power operational amplifiers. With an excellent bandwidt h of 1MHz,a slew rate of1V/µs,and a quiescent c urrent of 28µA peramplifier at 5V,the LMV324IDR (MS) family can bedesigned into a wide range of applications.

The LMV324IDR(MS) op-amps are designed to p rovideoptimal performance in low voltage and low power systems.The input common-modevoltage r ange includes ground,and themaximum input offs et voltage are 3mV.Theseparts provide rail-to-rail output swing into heavyloads.

The LMV324IDR(MS) families of operational am plifiersare specified at the full temperature range of -40°C to +125°°C under single or dual powers upplies of 1.5V to 5.5V.

FEATURES

- Input Offset Voltage:1mV (Typical)
- Low Supply Current:28µA(Vs=5V)
- Supply Range:1.8V to 5.5V
- Gain Bandwidth:1MHz(Vs=5V)
- Slew rate:1V/us (Vs=5V)
- Rail-to-Rail Input and Output
- Low Cost
- Micro size Packages:
- LMV324IDR(MS:SOIC-14

APPLICATIONS

- Battery and Power Supply Control
- Audio Outputs
- Smoke/Gas/Environment Sensors
- Portable Equipment and Mobile Devices
- Sensor Interfaces
- Active Filters
- Medical Equipment

PACKAGE OUTLINE	Pin Assi	gnments	Marking
SOIC-14	OUTA 1 -INA 2 +INA 3 V+ 4 +INB 5 -INB 6 -INB 6 -INB 7	14 OUTD 13 -IND 12 +IND 11 V- 10 +INC 9 -INC 8 OUTC	LMV324IDR MS*** • Note: ***=batch

Pin Configuration and Functions





Pin Description

PIN		I/0	DECODIDITION	
NAME	Number	1/0	DESCRIPTION	
+INA	3		Noninverting input, channel A	
+INB	5		Noninverting input, channel B	
+INC	10		Noninverting input, channel C	
+IND	12		Noninverting input, channel D	
-INA	2		Inverting input, channel A	
-INB	6		Inverting input, channel B	
-INC	9		Inverting input, channel C	
-IND	13		Inverting input, channel D	
OUTA	1	0	Output, channel A	
OUTB	7	0	Output, channel B	
OUTC	8		Output, channel C	
OUTD	14	0	Output, channel D	
V-	4		Negative (lowest)power supply	
V+	11		Positive (highest)power supply	

TYPICAL APPLICATION

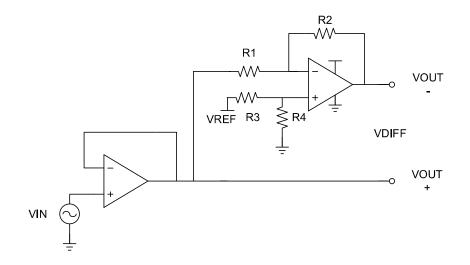


Figure 1. Typical Application



Detailed Description

Oyerview

The LMV324IDR(MS) devices are a low power, unity-gain stable, rail-to-rail operational amplifier that operate in a single-supply voltage range of 1.8V to 5.5V (\pm 0.9V to \pm 2.75V). A high supply voltage of 6V(absolute maximum) can permanently damage the amplifier. Rail-to-rail input and output wobbles significantly increase the dynamic range, especially in low-supply applications. Good layout practices require that a 0.1 uF capacitor be used where it is tightly threaded through the power supply pin.

Phase Reversal Protection

The LMV324IDR(MS) devices have internal phase-reversal protection.Many op amps exhibit phase reversal when the input is driven beyond the linear common-mode range.This condition is most often encountered in noninverting circuits when the input is driven beyond the specified common-mode voltage range,causing the output to reverse into the opposite rail.The input of the LMV324IDR(MS) prevents phase reversal with excessive commonmode voltage.Instead,the appropriate rail limits the output voltage

Typical Applications

1 Voltage Follower

As shown in Figure 12, the voltage gain is 1. With this circuit, the output voltage Vour is configured to be equal to the input voltage Vin. Due to the high input impedance and low output impedance, the circuit can also stabilize the output voltage, the output voltage expression is Detailed Descriptio



SPECIFICATIONS

Absolute Maximum Ratings⁽¹⁾

		MIN	MAX	UNIT
	Supply Voltage		6	V
Voltage	Signal Input Terminals Voltage ⁽²⁾	(V-) - 0.5	(V+) + 0.5	V
	Signal Input Terminals Voltage ⁽³⁾	(V-) - 0.5	(V+) + 0.5	V
	Signal Input Terminals Current ⁽²⁾	-10	10	mA
Current	Signal output Terminals Current ⁽³⁾	-200	200	mA
	Output Short-Circuit ⁽⁴⁾		inuous	
	Operating Temperature Range	-55	125	°C
θ_{JA}	Storage Temperature Range	-65	150	°C
	Junction Temperature	-40	150	°C

(1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.

- (2) Input terminals are diode clamped to the power-supply rails. Input signals that can swing more than 0.5V beyond the supply rails should be current limited to 10mA or less.
- (3) Output terminals are diode-clamped to the power-supply rails. Output signals that can swing more than 0.5V beyond the supply rails should be current-limited to ±200mA or less.
- (4) Short-circuit to ground, one amplifier per package.

ESD Ratings

			VALUE	UNIT
		Human-Body Model (HBM)	±2000	V
$V_{(ESD)}$	Electrostatic discharge	Charged-Device Model (CDM)	±500	V
		Machine Model	100	V

Recommended Operating Conditions

		MIN	MAX	UNIT
Supply voltage,	Single-supply	1.5	5.5	V
Vs= (V+) - (V-)	Dual-supply	±0.75	±2.75	V



ELECTRICAL CHARACTERISTICS (Vs = +5V)

At $T_A = 25^{\circ}$ C, $V_{CM}=V_{OUT}=V_S$ /2, unless otherwise noted.

	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
OFFSET	VOLTAGE					
Vos	Input Offset Voltage		-3	±1	3	mV
dV _{OS} /dT	Input Offset Voltage Average Drift	T _A = -55°C to 125°C		1.8		µV/°C
INPUT C	URRENT					
B	Input Bias Current			5		pА
os	Input Offset Current			1		pА
NOISE						
V _N	Input Voltage Noise	f=0.1Hz to 10Hz		20		μV _{PP}
en	Input Voltage Noise Density	f=1kHz		65		nV/√Hz
INPUT V	OLTAGE					
V_{CM}	Common-Mode Voltage Range		V _s 0.1		V _{S+} +0.1	V
CMRR	Common-Mode Rejection Ratio	V_{CM} =0.1V to 4V	70	80		dB
FREQUE	NCY RESPONSE					
GBW	Gain-Bandwidth Product			1		MHz
SR	Slew Rate	G = +1, V _{IN} =2V Step		1		V/us
t _s	Settling Time to 0.1%	G = +1, V _{IN} =2V Step		2.5		us
OUTPUT						
Av	Open-Loop Voltage Gain	V _{OUT} =0.1V to 4.9V R _L =100kΩ	80	100		dB
V _{OUT} . swing	Output Swing from Rail	R∟=100kΩ			5	mV
sc	Output Short-Circuit Current	Source current		45		mA
130		Sink current		70		mA
$C_L^{(1)}$	Capacitive Load Drive	G = +1, V _{IN} =0.2V Step			1000	pF

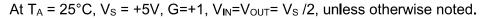


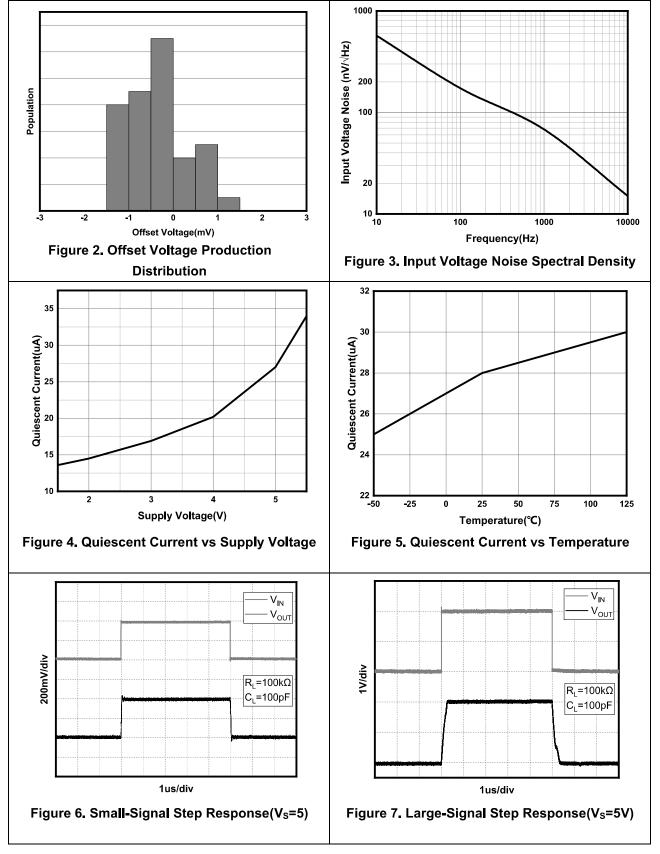
POWER SUPPLY						
PSRR	Power-Supply Rejection Ratio	$V_{\rm S}$ =1.5V to 5.5V	80	90		dB
Vs	Operating Voltage Range		1.5		5.5	V
Ιq	Quiescent Current/Amplifier	I ₀ =0A		28	40	uA

(1) Capacitive load drive means that above a given maximum value, the output waveform will oscillate under the step response.



TYPICAL CHARACTERISTICS

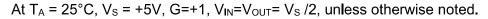


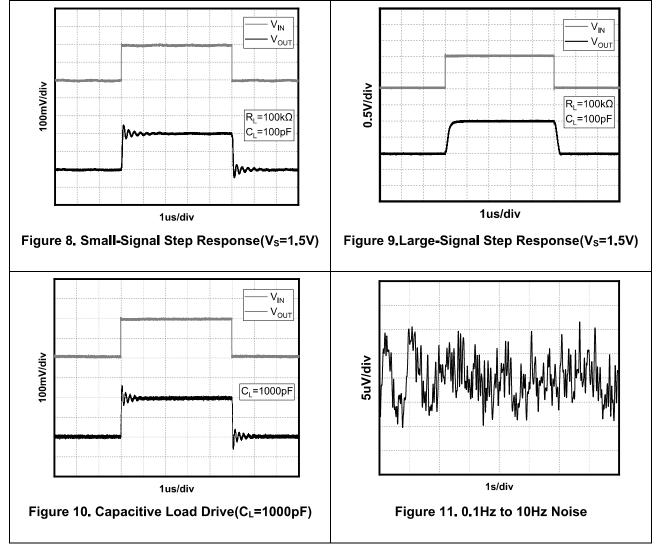






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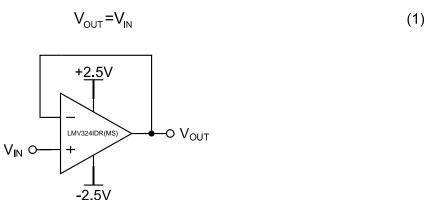


Figure 12. Voltage Follower

2 Inverting Proportional Amplifier

As shown in Figure 13, for a reverse-phase proportional amplifier, the input voltage V_{IN} is amplified by a voltage gain that depends on the ratio of R1 to R2. The output voltage V_{OUT} is inversely with the input voltage V_{IN} . The input impedance of the circuit is equal to R1, and the output voltage expression is

$$V_{OUT} = -\frac{R2}{R1} V_{IN}$$
⁽²⁾



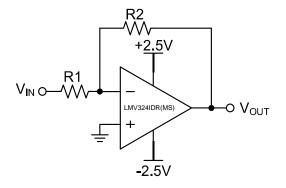


Figure 13. Inverting Proportional Amplifier

3 Noninverting Proportional Amplifier

As shown in Figure 14, for a noninverting amplifier, the input voltage V_{IN} is amplified by a voltage gain that depends on the ratio of R1 to R2. The output voltage V_{OUT} is in phase with the input voltage V_{IN} . In fact, this circuit has a high input impedance because its input side is the same as the input side of the operational amplifier. The output voltage expression is

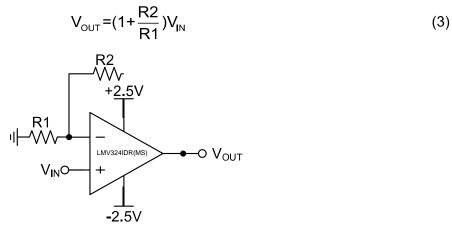


Figure 14. Noninverting Proportional Amplifier

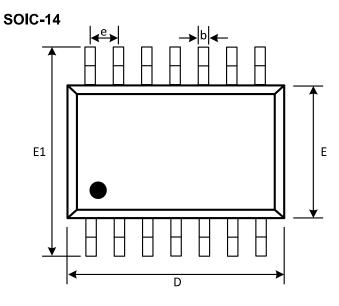
Layout Guidelines

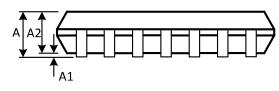
Attention to good layout practices is always recommended. Keep traces short. When possible, use a PCB ground plane with surface-mount components placed as close to the device pins as possible. Place a 0.1uF capacitor closely across the supply pins.

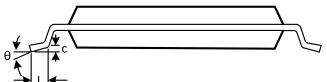
These guidelines should be applied throughout the analog circuit to improve performance and provide benefits such as reducing the EMI susceptibility.



PACKAGE DESCRIPTION







(Unit: mm)

Symbol	Min	Мах	
A	1.350	1.750	
A1	0.100	0.250	
A2	1.350	1.550	
b	0.310	0.510	
с	0.100	0.250	
D	8.450	8.850	
е	1.270(BSC)		
E	5.800	6.200	
E1	3.800	4.000	
L	0.400	1.270	
θ	0°	8°	

REEL SPECIFICATION

P/N	PKG	QTY
LMV324IDR(MS)	SOIC-14	2500



LMV324IDR(MS)

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